

For EMI Filtering and ESD Protection.

#### FEATURES

- EMI/RFI filtering.
- ESD Protection to IEC 61000-4-2 Level 4.
- Low insertion loss.
- Good attenuation of high frequency signals.
- Low clamping voltage.
- Low operating and leakage current.

#### APPLICATIONS

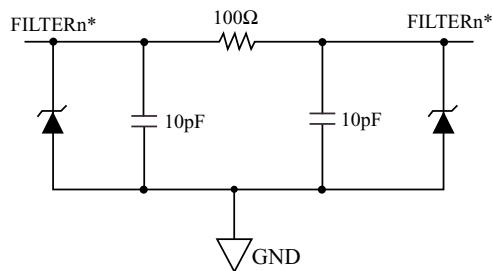
- Cell phone handsets.
- RF communications equipment.

#### MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Power Per Resistor	$P_R$	100	mW
Power Dissipation	$*P_D$	400	
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55 ~ 150	°C

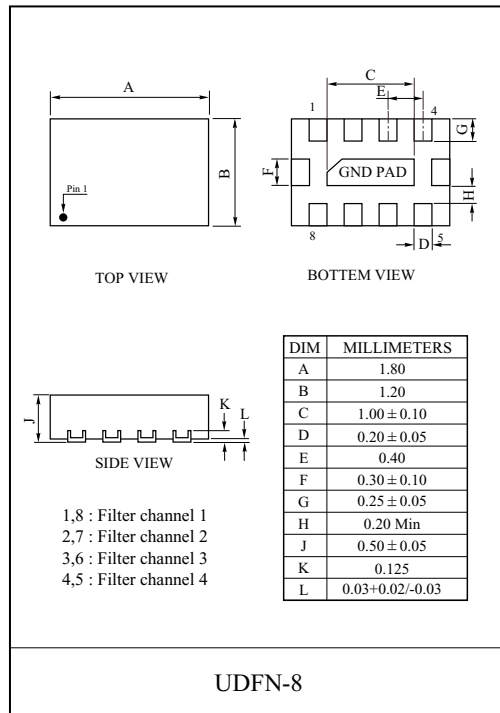
\* Total Package Power Dissipation

#### EQUIVALENT CIRCUIT

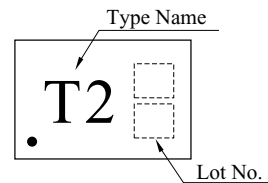


#### ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Stand-Off Voltage	$V_{RWM}$	-	-	-	5	V
Reverse Breakdown Voltage	$V_{BR}$	$I_t=1mA$	6	-	-	V
Reverse Leakage Current	$I_R$	$V_{RWM}=3V$	-	-	0.1	$\mu A$
Cutoff Frequency	$f_{3dB}$	$V_R=0V, Z_{SOURCE}=50 \Omega, Z_{LOAD}=50 \Omega$	-	150	-	MHz
Attenuation	$ S_{21} ^2$	$V_R=0V, f=800MHz\sim 3GHz, Z_{SOURCE}=50 \Omega, Z_{LOAD}=50 \Omega$	25	-	-	dB
Resistance	R	Between Input and Output	-	100	-	$\Omega$
Capacitance	C	$V_R=2.5V$ , Between I/O Pins and GND	-	20	-	pF

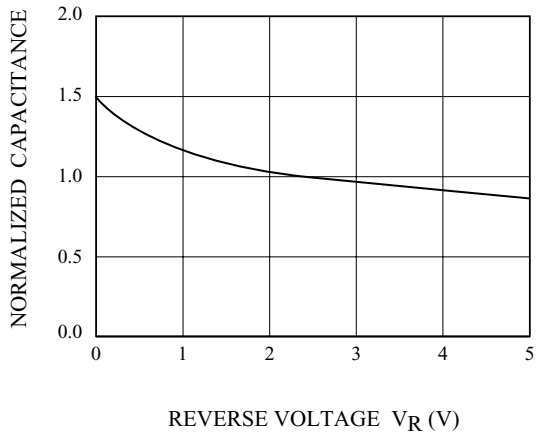


#### MARKING

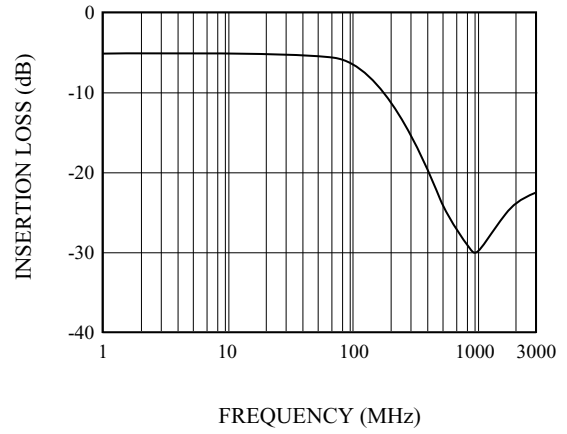


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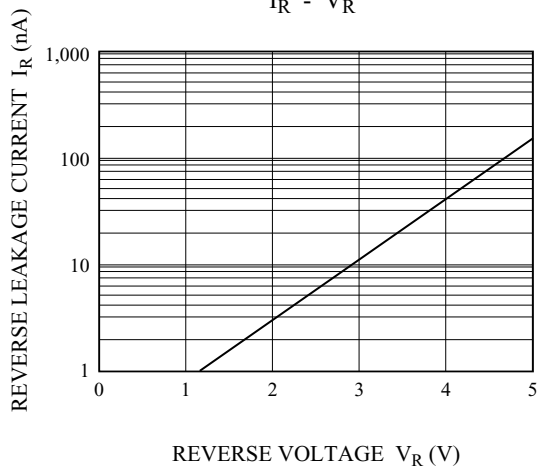
$C_J - V_R$



$S_{21} - f$



$I_R - V_R$



$R - T_a$

